

N-channel 30 V, 1.8 mΩ logic level MOSFET in TO-220Rev. 02 — 2 November 2010Product of

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- 1.3 Applications
 - DC-to-DC converters
 - Load switching

- Suitable for logic level gate drive sources
- Motor control
- Server power supplies

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	[1]	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	270	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 13}}; \\ \text{see } \underline{\text{Figure 12}} \end{array}$	[2]	-	1.6	1.8	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 4.5 V; I _D = 25 A;		-	22	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>		-	83	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $I_D = 100 \text{ A}; V_{sup} \le 30 \text{ V};$ $R_{GS} = 50 \Omega;$ unclamped		-	-	1.1	J

[1] Continuous current is limited by package.

[2] Measured 3 mm from package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R8-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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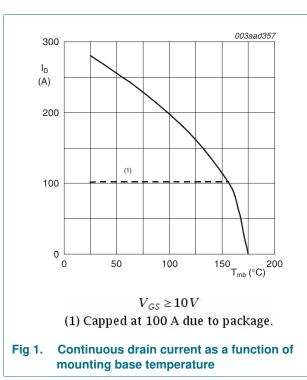
4. Limiting values

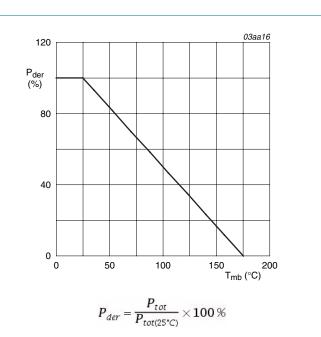
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	1120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	270	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1120	А
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω ; unclamped		-	1.1	J

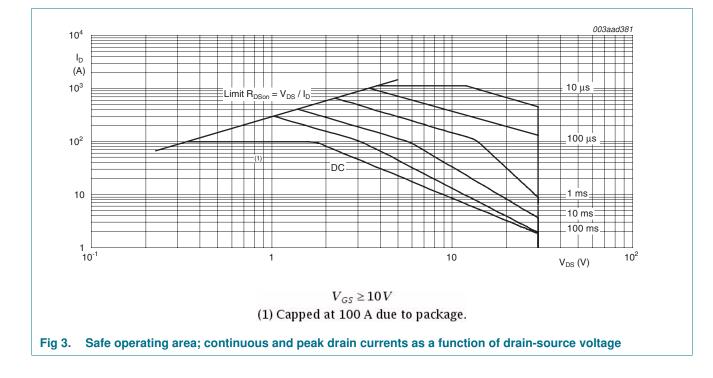
[1] Continuous current is limited by package.







PSMN1R8-30PL



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Ρ

tp

δ

Thermal characteristics 5.

single shot

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.3	0.56	K/W
1			++++++		003aad080	

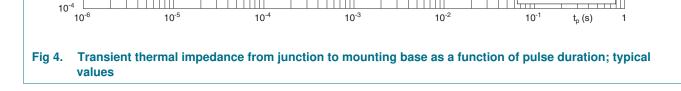
Thermal characteristics Table 5.

0.05

0.02

10⁻²

10⁻³



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6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$\label{eq:ID} \begin{split} I_D &= 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 175 ^\circ\text{C}; \\ \text{see } \overline{Figure \ 11} \end{split}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	4	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	200	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.8	2.3	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see Figure 13	-	-	3.42	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 13</u>	-	-	2.4	mΩ
	V_{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 13</u>	-	-	4.73	mΩ	
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 13; see Figure 12	11 -	1.6	1.8	mΩ
R _G	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	170	-	nC
		$I_{D} = 0 \text{ A}; V_{DS} = 0 V; V_{GS} = 10 V$	-	158	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	83	-	nC
Q _{GS}	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	29	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	17	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	12	-	nC
Q _{GD}	gate-drain charge		-	22	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.6	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	10180	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	2000	-	pF
C _{rss}	reverse transfer capacitance		-	872	-	pF

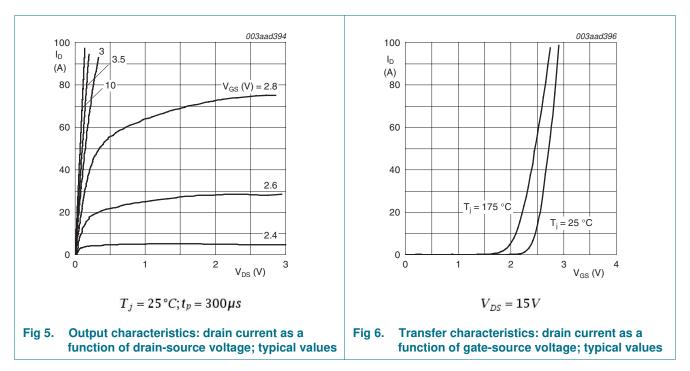
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Table 6. Characteristics ...continued

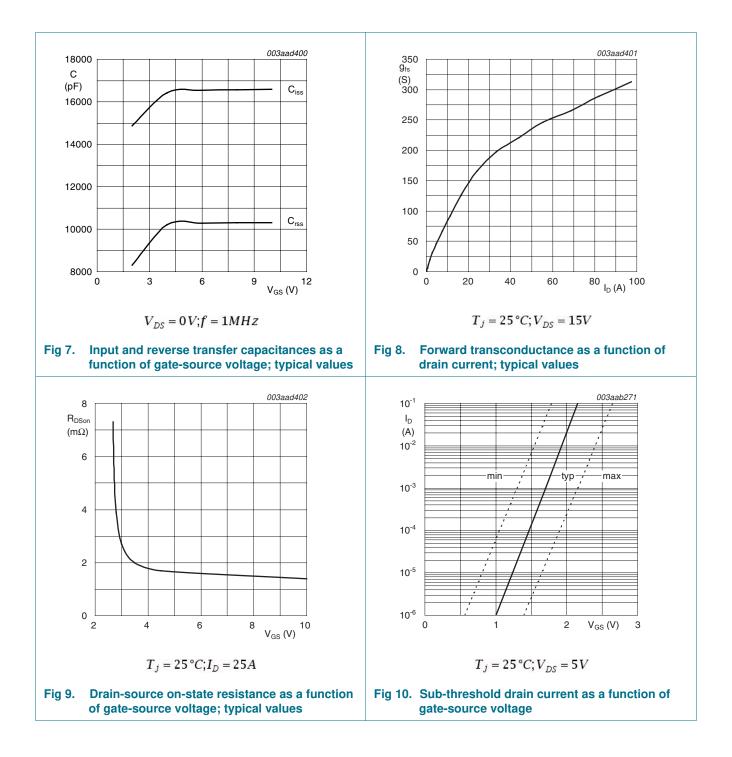
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	$V_{DS} = 12 \text{ V}; \text{R}_{L} = 0.5 \Omega; \text{V}_{GS} = 4.5 \text{ V};$	-	92	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	156	-	ns
t _{d(off)}	turn-off delay time		-	135	-	ns
t _f	fall time		-	69	-	ns
Source-drai	in diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 30 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s;$	-	64	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 12 V$	-	60	-	nC

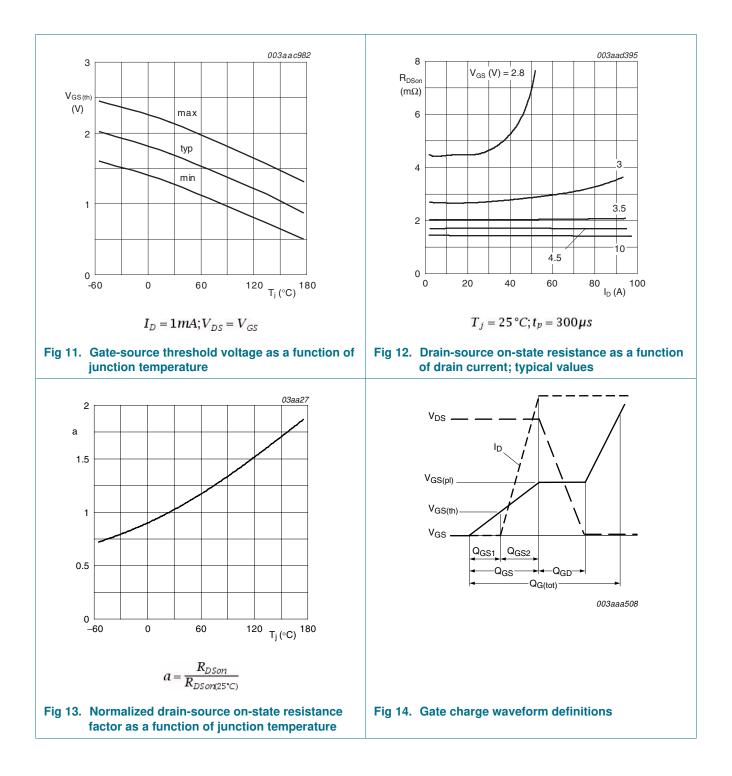
[1] Measured 3 mm from package.



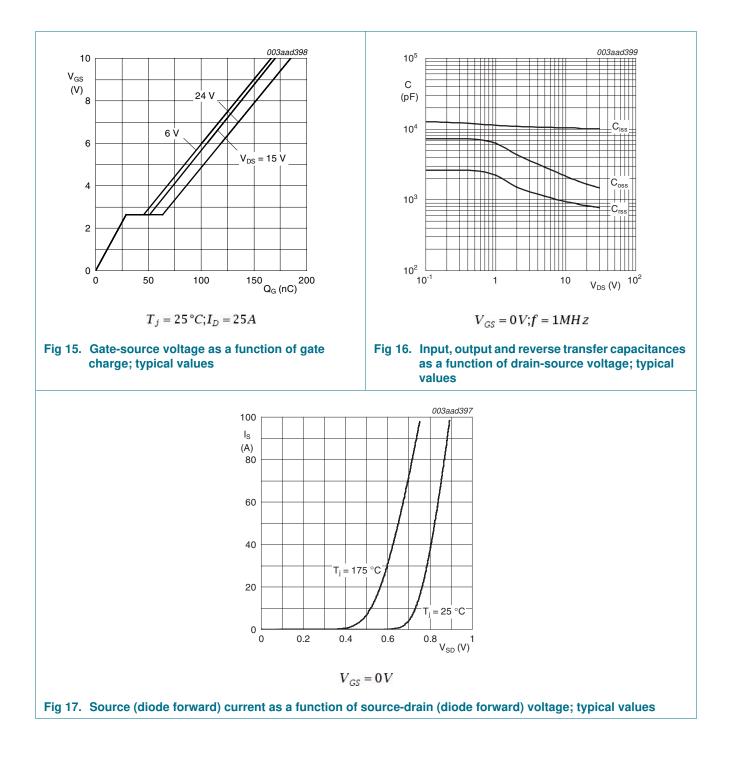
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PSMN1R8-30PL



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Package outline 7.

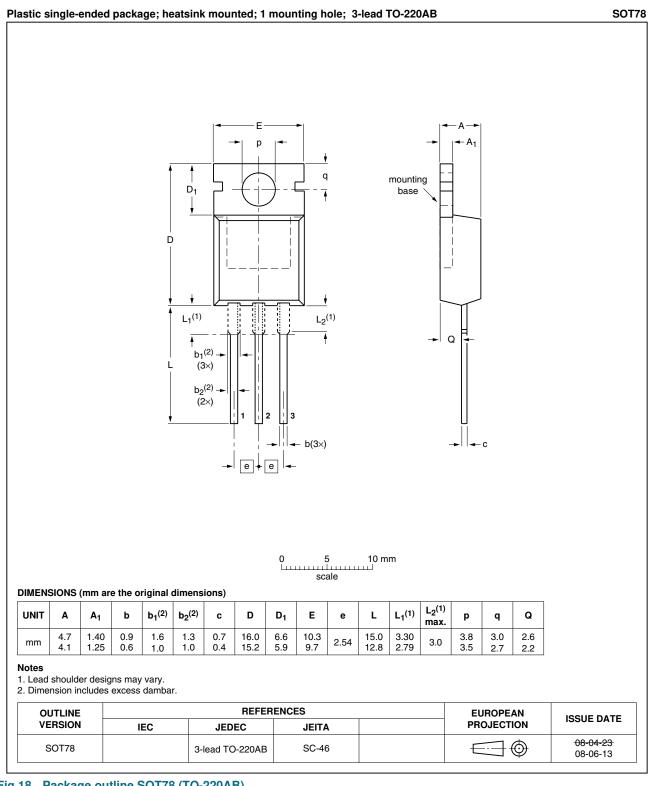


Fig 18. Package outline SOT78 (TO-220AB)

PSMN1R8-30PL **Product data sheet**

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R8-30PL v.2	20101102	Product data sheet	-	PSMN1R8-30PL v.1
Modifications:	Status changeVarious chang	d from objective to product. es to content.		
PSMN1R8-30PL v.1	20100218	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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